

NAND-TYPE FLASH MEMORY DEVICES AND METHODS OF FABRICATING THE  
SAME

Abstract of the Disclosure

NAND-type flash memory devices and methods of fabricating the same are provided.

- 5 The NAND-type flash memory device includes a plurality of isolation layers running parallel with each other, which are formed at predetermined regions of a semiconductor substrate. This device also includes a string selection line pattern, a plurality of word line patterns and a ground selection line pattern which cross over the isolation layers and active regions between the isolation layers. Source regions are formed in the active regions adjacent to the ground selection
- 10 line patterns and opposite the string selection line pattern. The source regions and the isolation layers between the source regions are covered with a common source line running parallel with the ground selection line pattern.

J:\SAM\0130DIV\0130divapp.wpd